

# PSMN5R0-40MSH

N-channel 40 V, 5 m $\Omega$ , standard level MOSFET in LFPAK33 using NextPower-S3 technology

27 April 2020

**Product data sheet** 

### 1. General description

85 A, standard level N-channel enhancement mode MOSFET in 175 °C LFPAK33 package using advanced TrenchMOS Superjunction technology. This product has been designed and qualified for high efficiency applications at high switching frequencies.

#### 2. Features and benefits

- Avalanche rated, 100% tested
- NextPower-S3 technology delivers 'superfast switching with soft body-diode recovery'
- Low Q<sub>RR</sub>, Q<sub>G</sub> and Q<sub>GD</sub> for high system efficiency, especially at high switching frequencies
- Low spiking and ringing for low EMI designs
- High reliability clip bonded and solder die attach Mini Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Exposed leads can be wave soldered, visual solder joint inspection and high quality solder joints
- · Low parasitic inductance and resistance

### 3. Applications

- · Secondary side synchronous rectification
- DC-to-DC converters
- Brushless DC motor drive
- LED lighting

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	85	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	83	W
Tj	junction temperature			-55	-	175	°C
Static characte	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ Fig. 10		-	3.9	5	mΩ
Dynamic characteristics							
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 20 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 10 V;		0.9	3	6	nC
Q <sub>G(tot)</sub>	total gate charge	Fig. 12; Fig. 13		13	21	29	nC

<sup>[1] 85</sup>A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.



## 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		D
2	S	source		
3	S	source		$G \longrightarrow G$
4	G	gate		mbb076 S
mb	D	Mounting base; connected to drain	1 2 3 4 LFPAK33 (SOT1210)	

## 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package	ickage					
	Name	Description	Version				
PSMN5R0-40MSH	LFPAK33	Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch	SOT1210				

## 7. Marking

#### **Table 4. Marking codes**

Type number	Marking code
PSMN5R0-40MSH	5H0S40

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	40	V
$V_{DSM}$	peak drain-source voltage	$t_p \le 20 \text{ ns}; f \le 500 \text{ kHz}; E_{DS(AL)} \le 200 \text{ nJ};$ pulsed		-	45	V
$V_{DGR}$	drain-gate voltage	25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ		-	40	V
$V_{GS}$	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	83	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	85	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	62	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 3		-	349	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drain	diode			'	'	'
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	85	А

Symbol	Parameter	Conditions		Min	Max	Unit
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$		-	349	Α
Avalanche rugg	edness					,
E <sub>DS(AL)S</sub>	source avalanche energy	$I_D$ = 29.6 A; $V_{sup} \le 40$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; $t_p$ = 107 μs	[2]	-	82.7	mJ
		$I_D$ = 20 A; $V_{sup} \le 40$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; $t_p$ = 245 μs	[2]	-	127.6	mJ
I <sub>AS</sub>	non-repetitive avalanche current	$V_{sup} \le 40 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega$	[2]	-	70	А

<sup>[1] 85</sup>A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

[2] Protected by 100% test

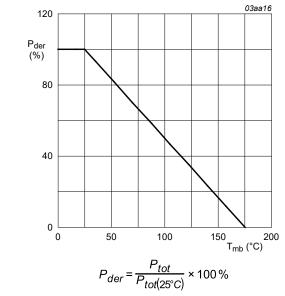
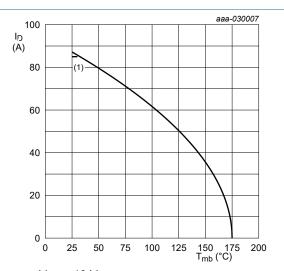
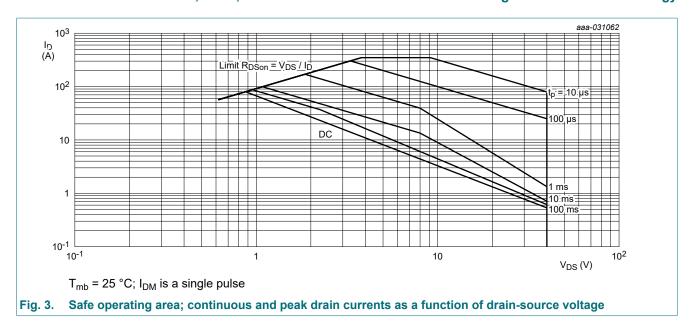


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



 $V_{GS} \ge 10 \text{ V}$  (1) 85A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

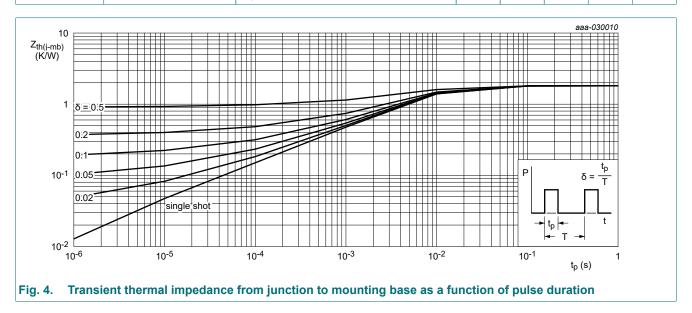
Fig. 2. Continuous drain current as a function of mounting base temperature



#### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	1.61	1.81	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 5 Fig. 6	-	50 130	-	K/W K/W



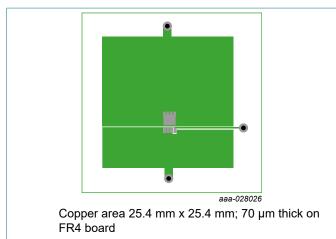
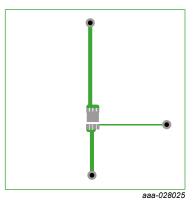


Fig. 5. PCB layout for thermal resistance from junction to ambient



70 µm thick copper on FR4 board

Fig. 6. PCB layout with minimum footprint for thermal resistance from junction to ambient

### 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	cteristics					
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	40	-	-	V
breakdown volta	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2.4	3	3.6	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>j</sub> ≤ 150 °C	-	-5.6	-	mV/K
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.01	1	μΑ
		V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	0.6	-	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ Fig. 10	-	3.9	5	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 20 A; $T_j$ = 175 °C; Fig. 11	-	-	10.9	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	0.3	0.8	2	Ω
Dynamic cha	aracteristics		'	'		
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 20 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 10 V; Fig. 12; Fig. 13	13	21	29	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V	-	11.8	-	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 20 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 10 V;	3.9	6.5	10	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 12; Fig. 13	2.6	4.3	6.5	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		1.3	2.2	3.3	nC
Q <sub>GD</sub>	gate-drain charge	1	0.9	3	6	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 20 A; V <sub>DS</sub> = 20 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	4.4	-	V

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	980	1507	2010	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	328	505	707	pF
C <sub>rss</sub>	reverse transfer capacitance		21	70	154	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 20 \text{ V}; \text{ R}_{L} = 0.8 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	6.5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	4.5	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	12.5	-	ns
t <sub>f</sub>	fall time		-	4.4	-	ns
Q <sub>oss</sub>	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	16	-	nC
Source-dra	in diode				'	
V <sub>SD</sub>	source-drain voltage	$I_S = 20 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 15$	-	0.82	1	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	25	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 20 V; <u>Fig. 16</u>	-	18	-	nC
t <sub>a</sub>	reverse recovery rise time		-	15	-	ns
t <sub>b</sub>	reverse recovery fall time		-	10	-	ns

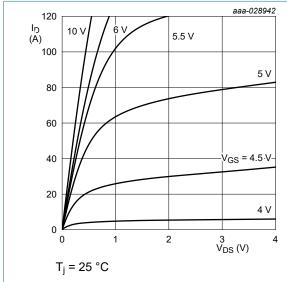


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

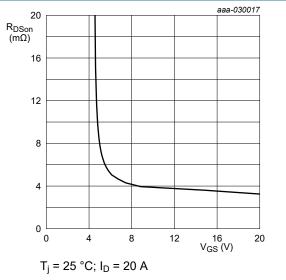


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

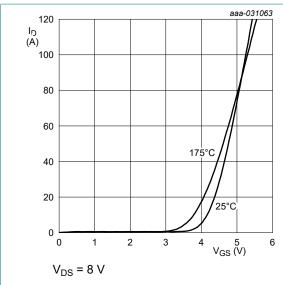


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

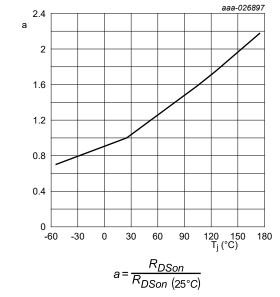


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

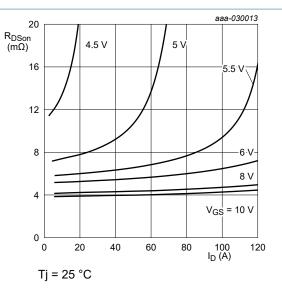


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

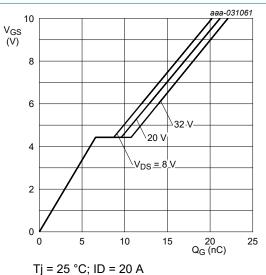


Fig. 12. Gate-source voltage as a function of gate charge; typical values

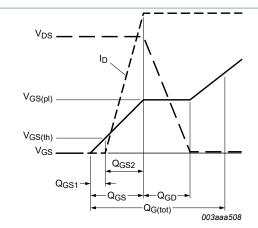
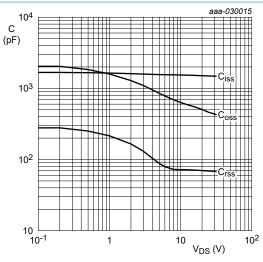


Fig. 13. Gate charge waveform definitions



 $V_{GS} = 0 V$ ; f = 1 MHz

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

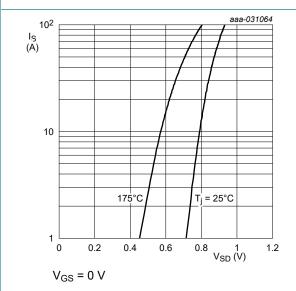


Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

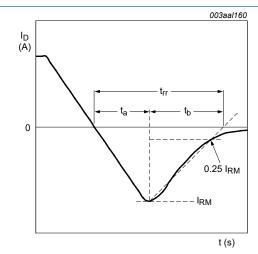


Fig. 16. Reverse recovery timing definition

## 11. Package outline

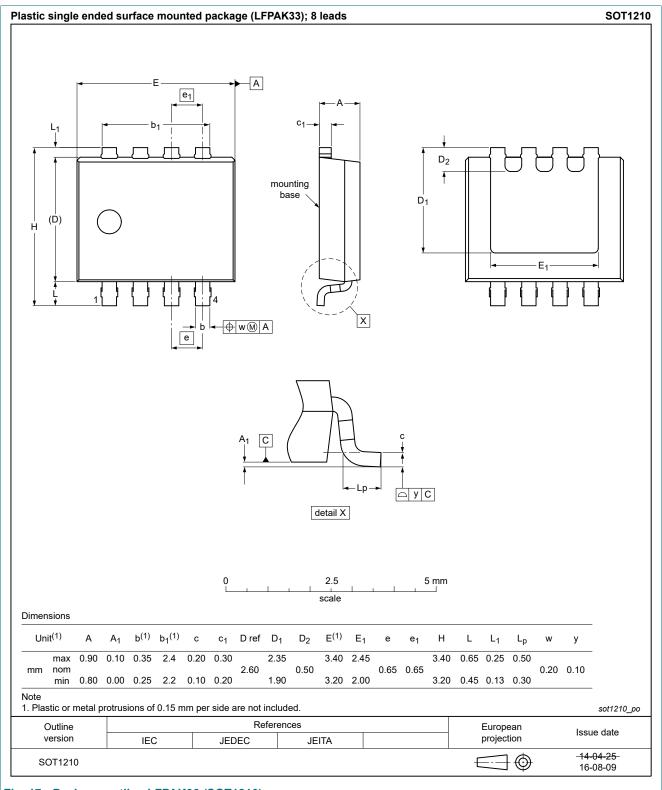
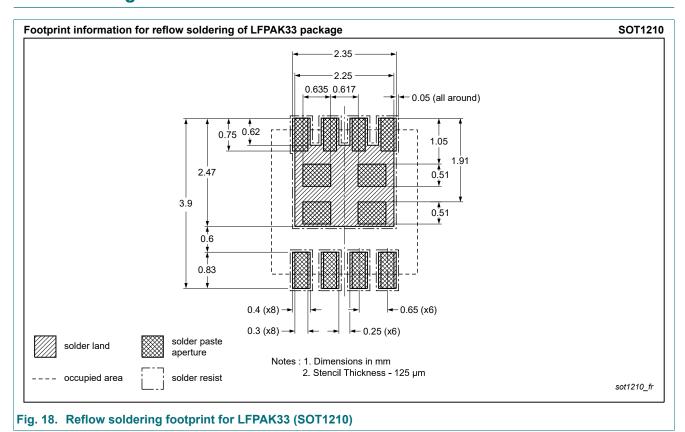


Fig. 17. Package outline LFPAK33 (SOT1210)

## 12. Soldering



### 13. Legal information

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